Progress meeting

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04/03/2013

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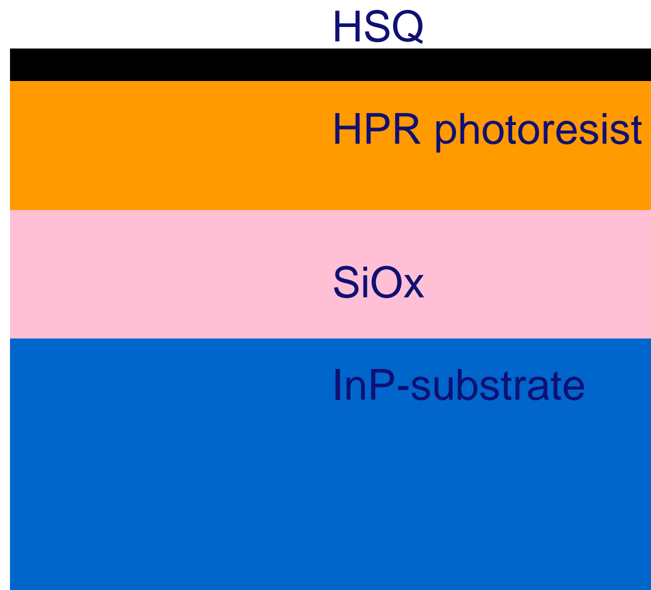
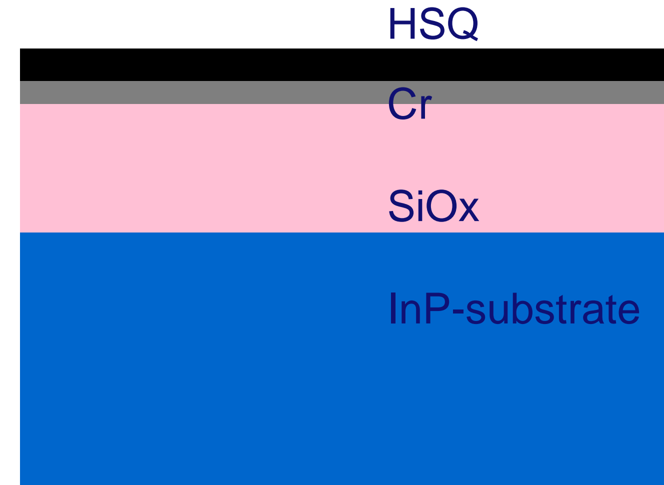
Where innovation starts

Testing of a new masking scheme

- Before



- Under test

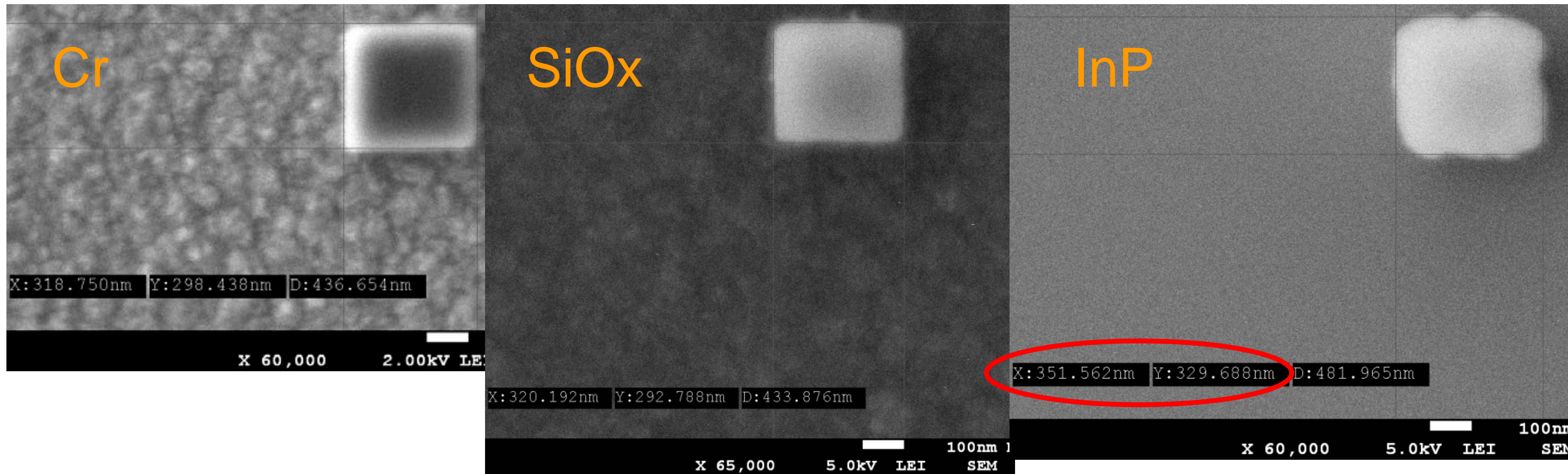


- Adhesion ✓
- Transferred roughness ? ✗

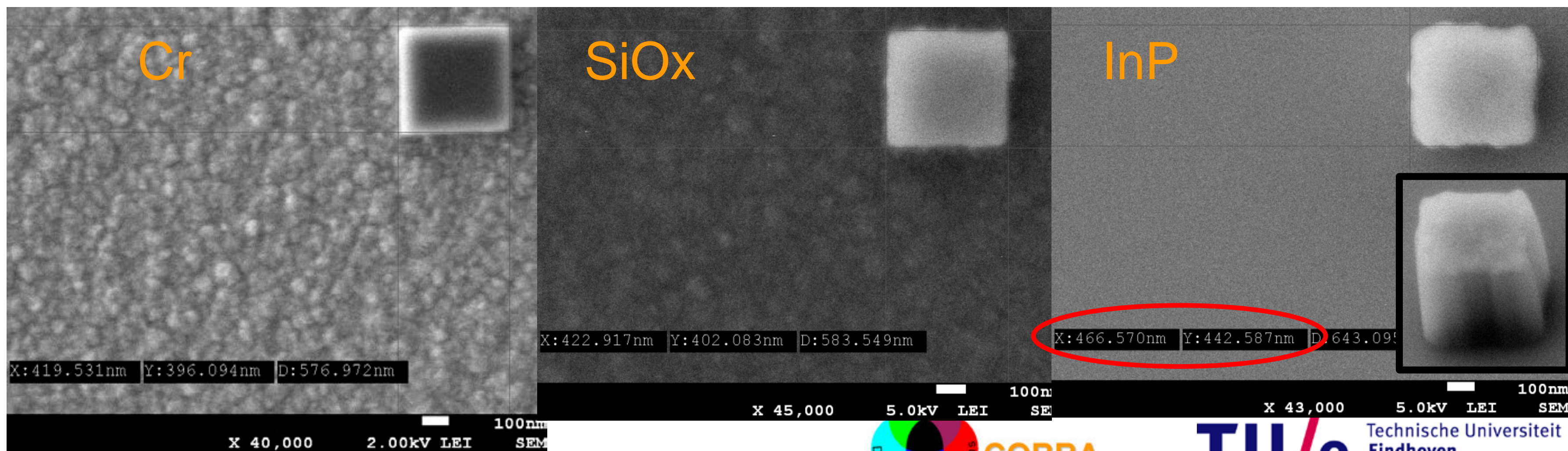
Etching with our standard recipies

- After development
- After Cr etching
- After SiOx etching

300x300nm



400x400nm



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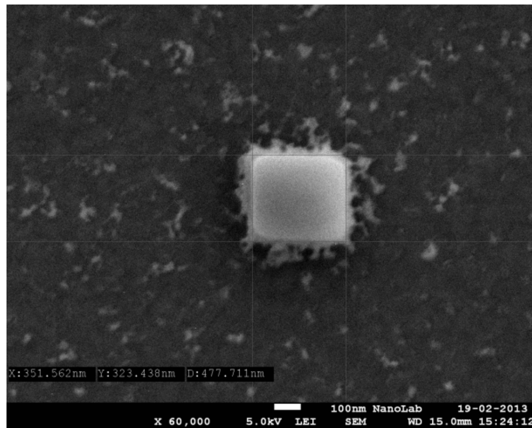
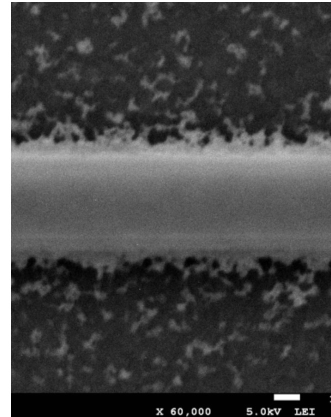
Other tests: increasing RF power → worse

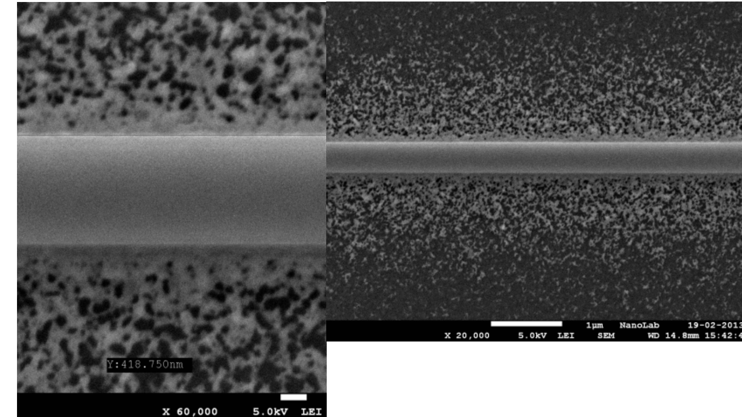
- **Increasing RF power:** RF = 10W



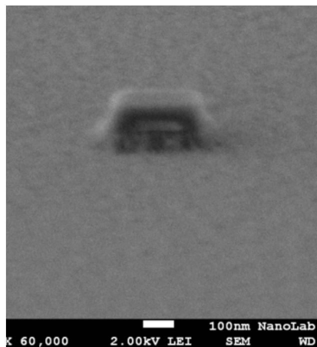
Low dose (d=4)

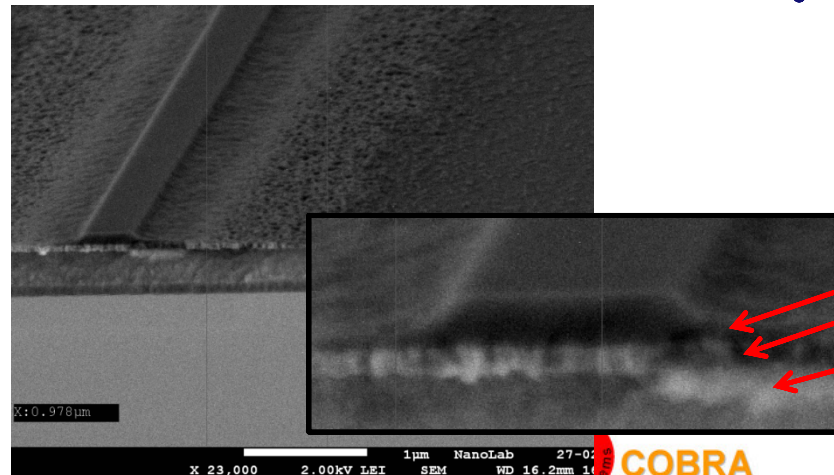


High dose



- **Side inspection**





HSQ
Cr
SiN

Reason:

- Strong back-reflection during EBL due to rough Cr

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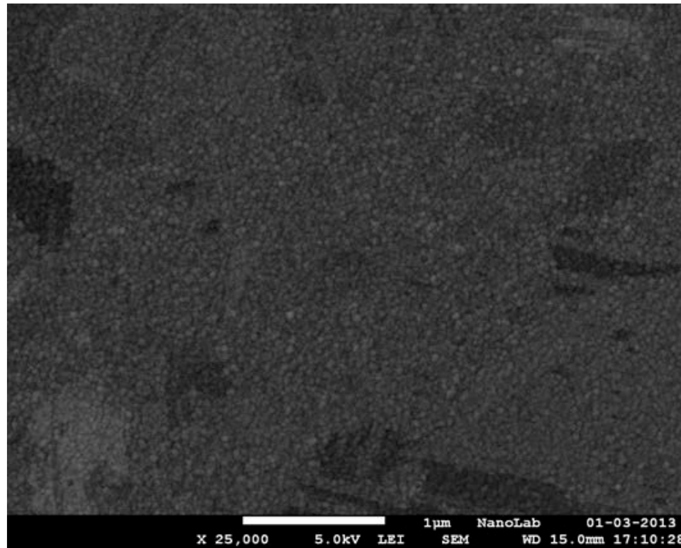
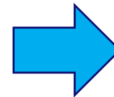
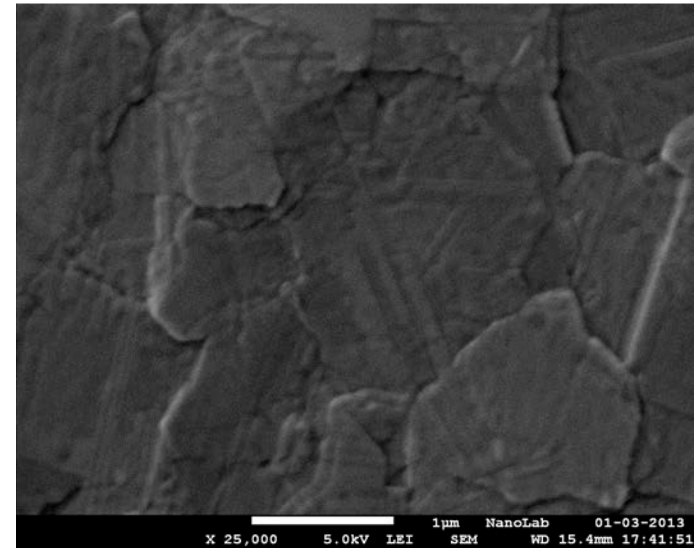
Silver annealing







- Just after deposition
- After RTA
  400 C, 1 min

Materials Devices Systems COBRA
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